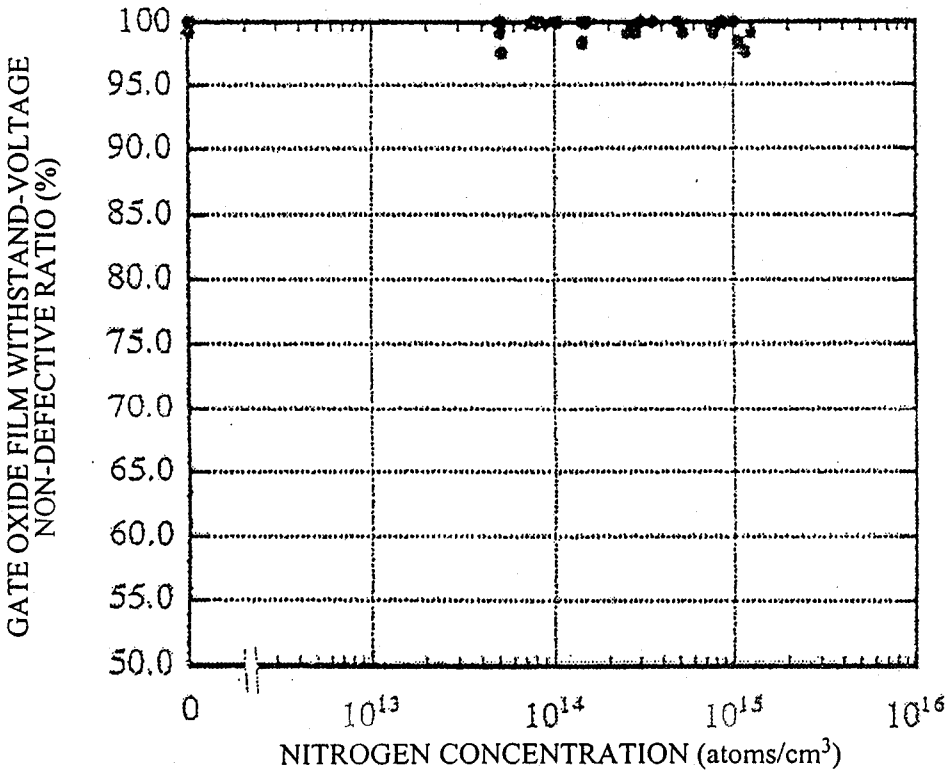
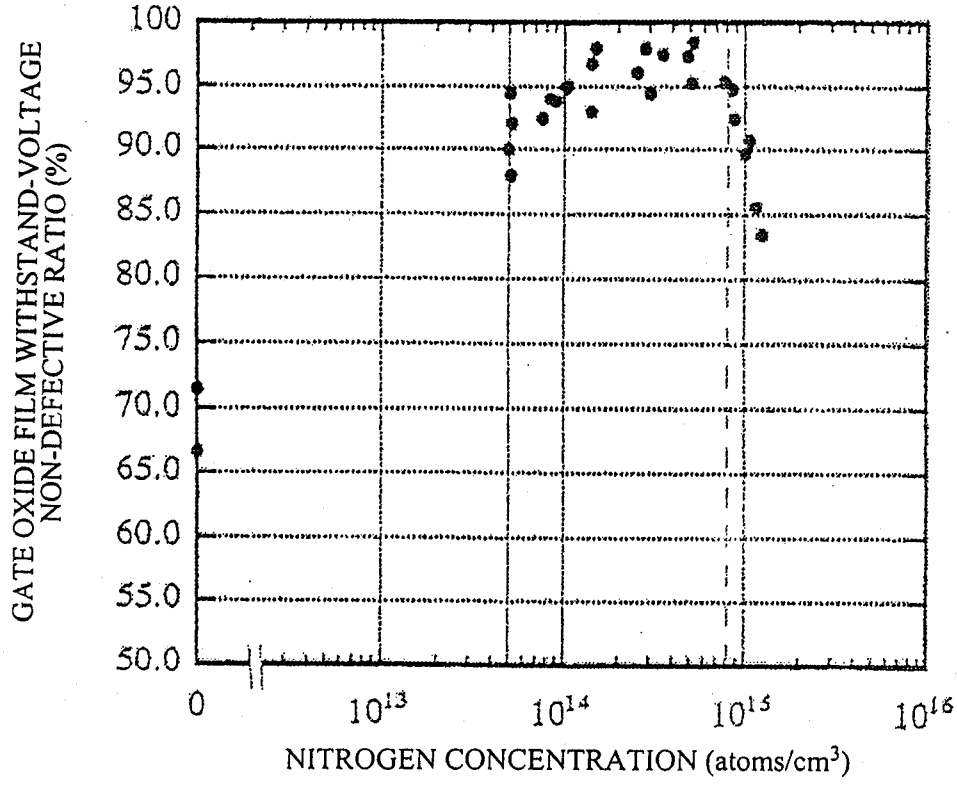
4 FEB 2004



RELATIONSHIP BETWEEN ADDED NITROGEN CONCENTRATION AND OXIDE FILM WITHSTAND-VOLTAGE NON-DEFECTIVE RATIO AFTER HYDROGEN ANNEALING

FIG.1

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RELATIONSHIP BETWEEN ADDED NITROGEN CONCENTRAION AND OXIDE FILM WITHSTAND-VOLTAGE NON-DEFECTIVE RATIO AFTER REMOVAL BY POLISHING SURFACE LAYER OF 3 μm AFTER HYDROGEN ANNEALING

FIG.2

4 FEB 2004

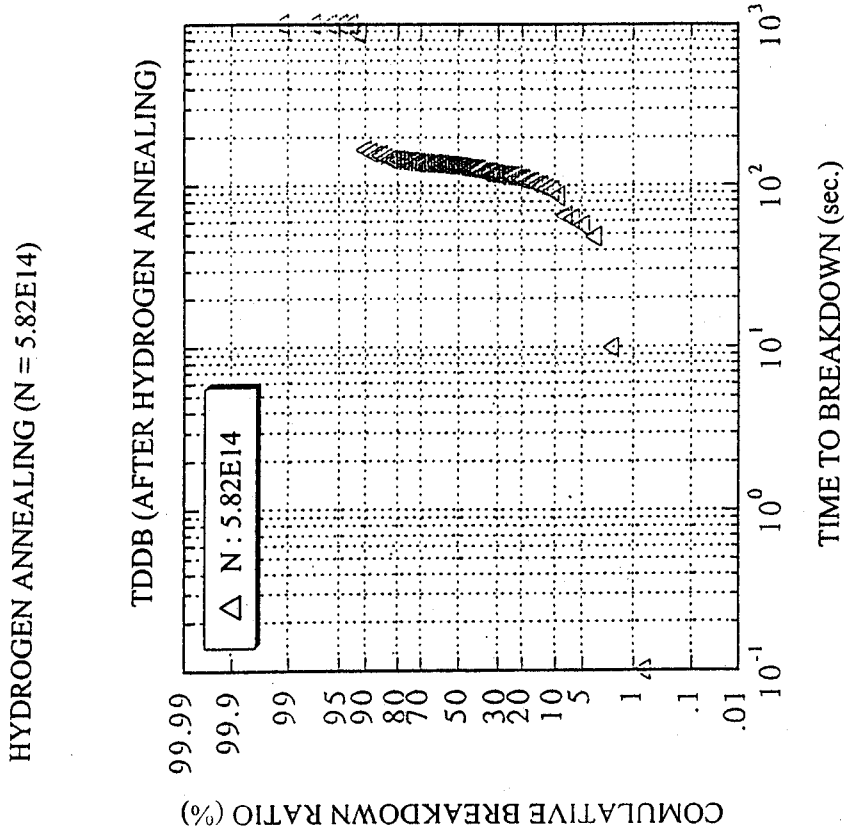


FIG.3(B)

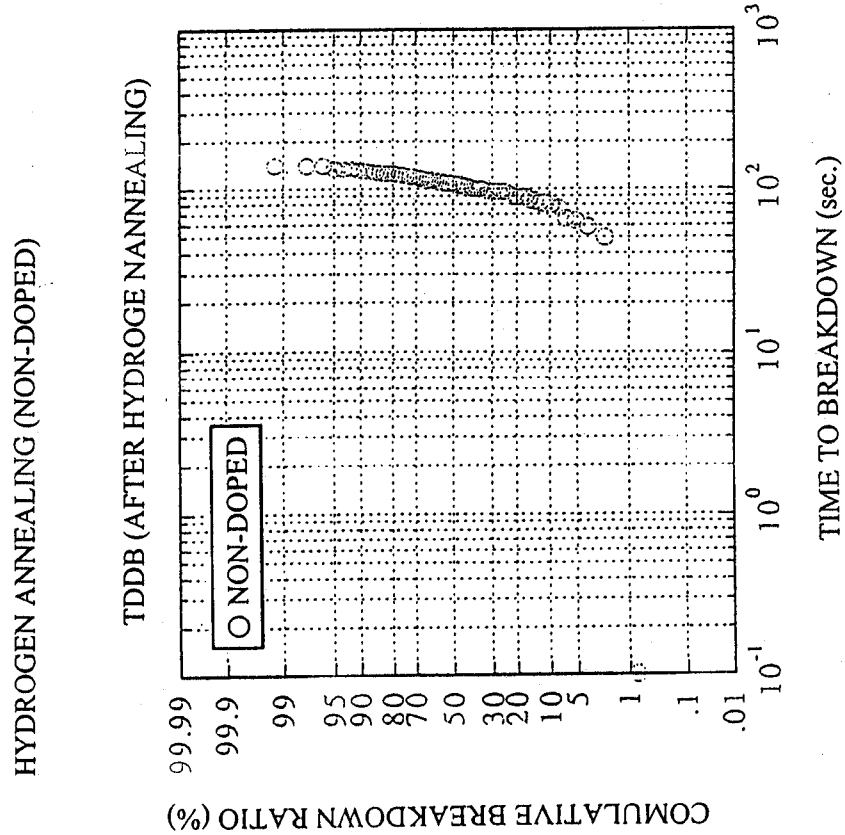


FIG.3(A)

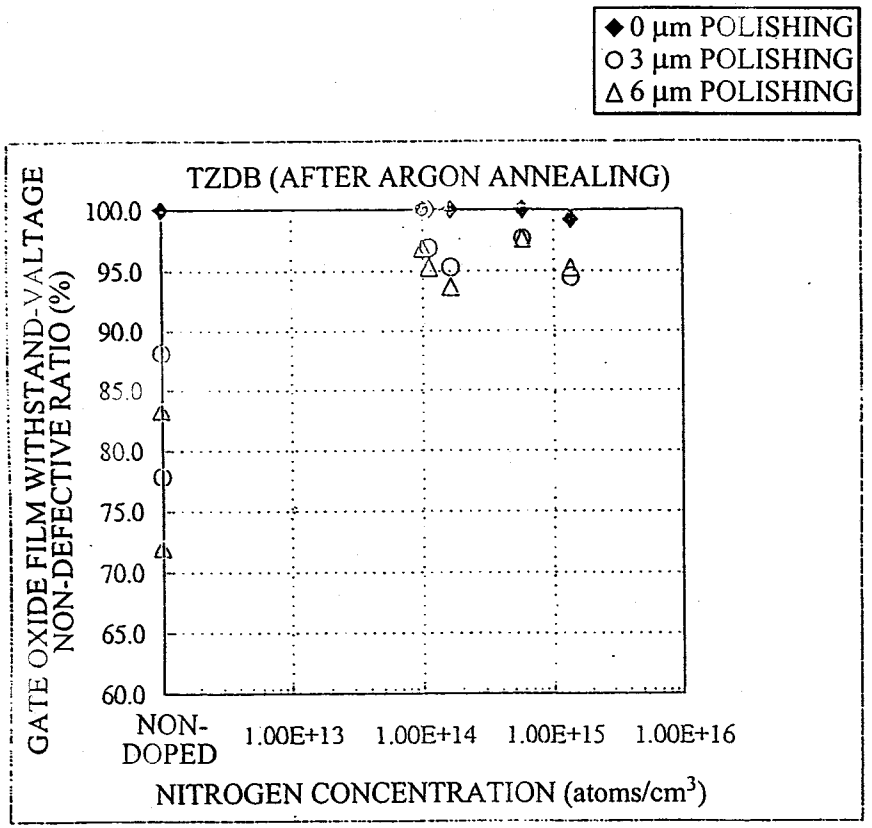


FIG.4(A)

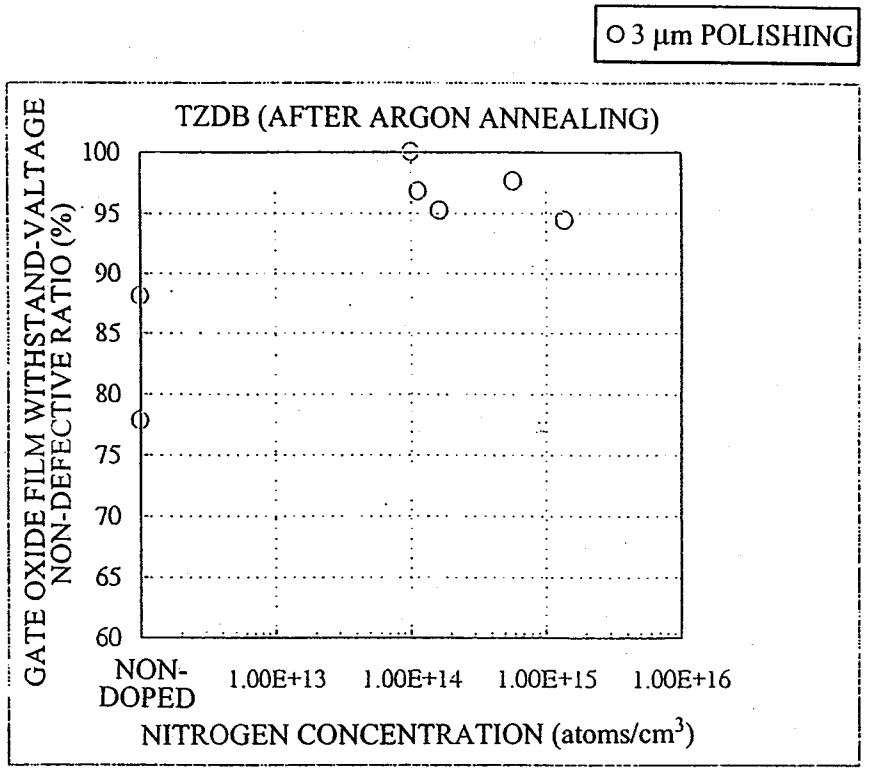


FIG.4(B)

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- 4 FEB 2004

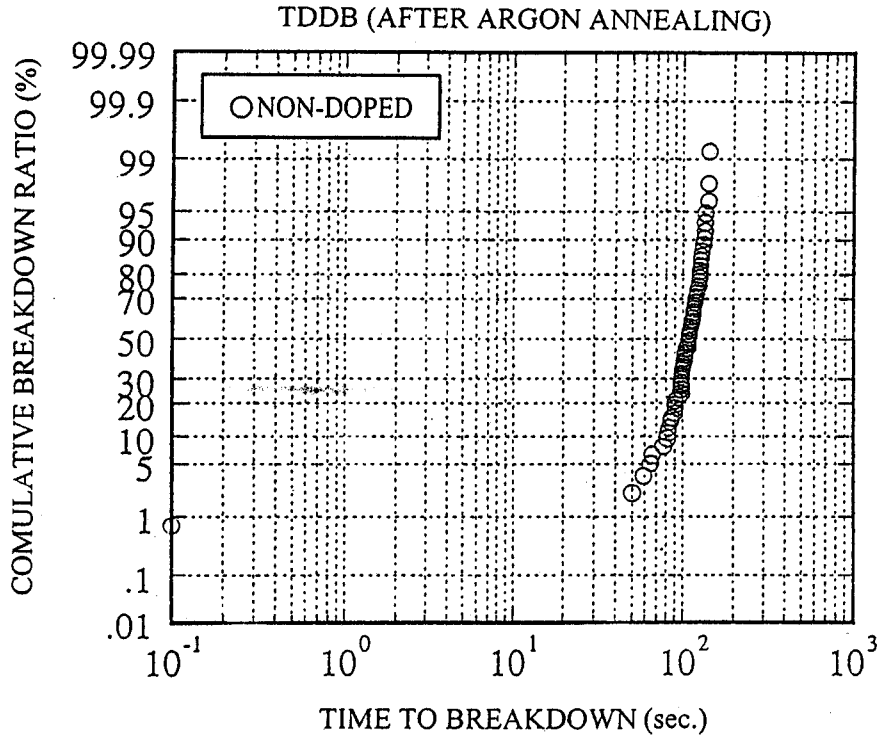


FIG.5(A)

- 4 FEB 2004

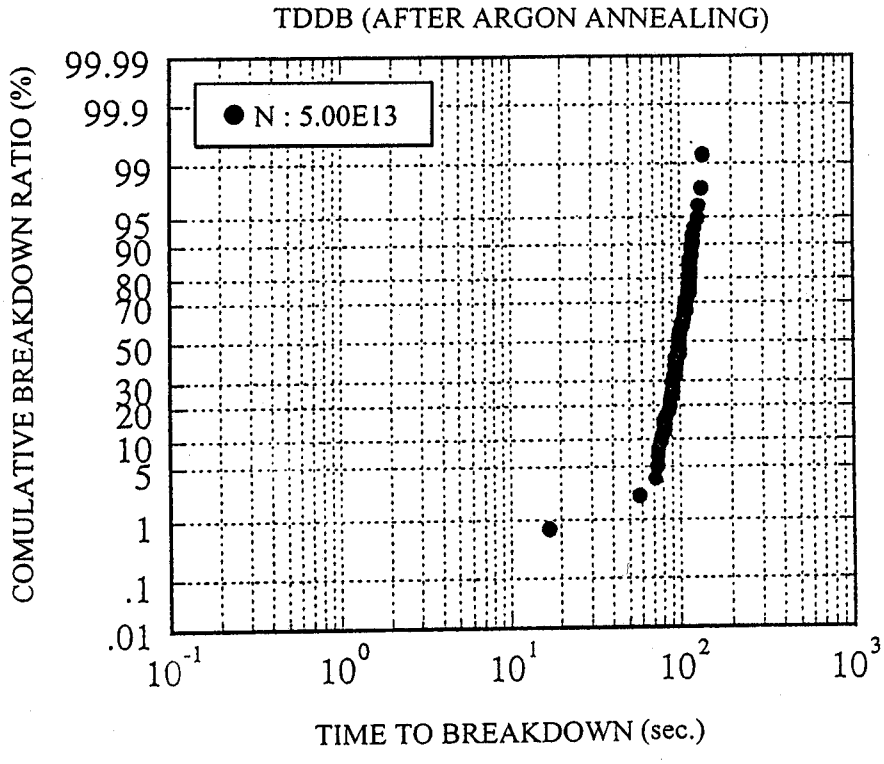


FIG.5(B)

- 4 FEB 2004

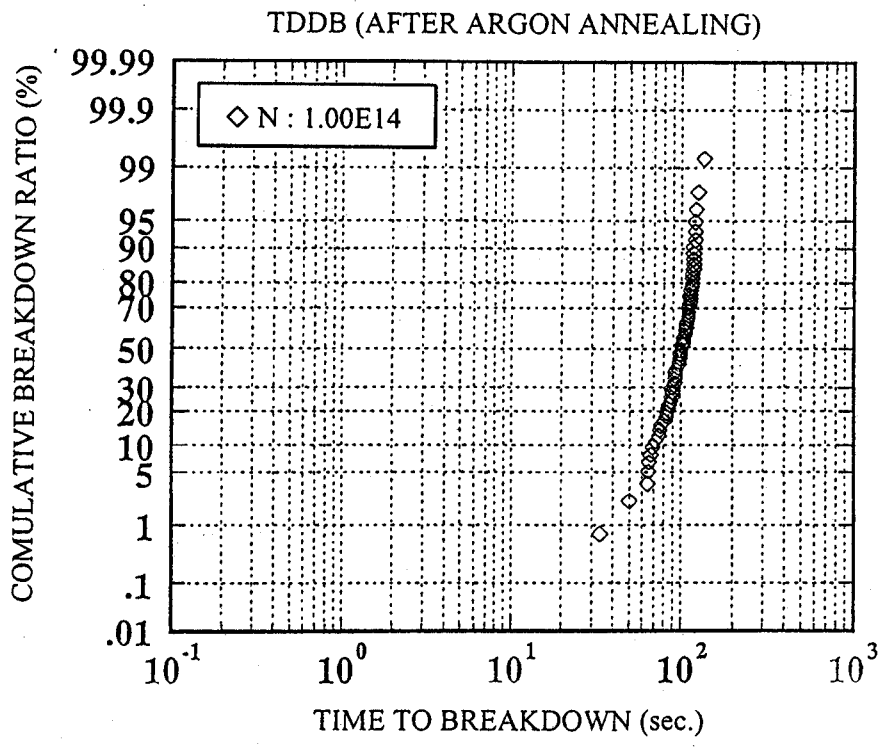


FIG.5(C)

4 FEB 2004

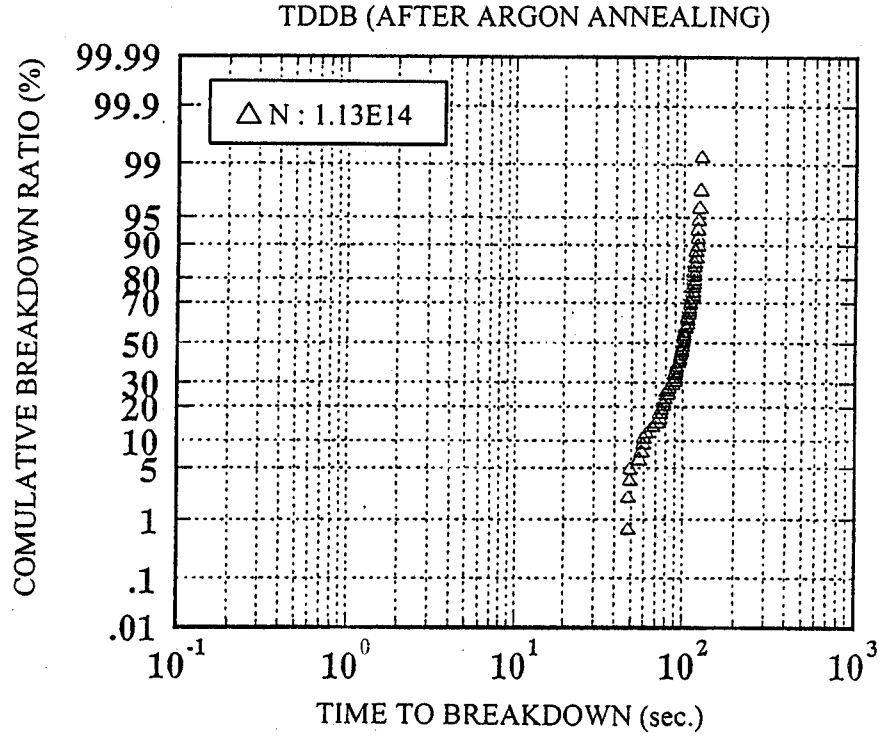


FIG.5(D)

4 FEB 2004

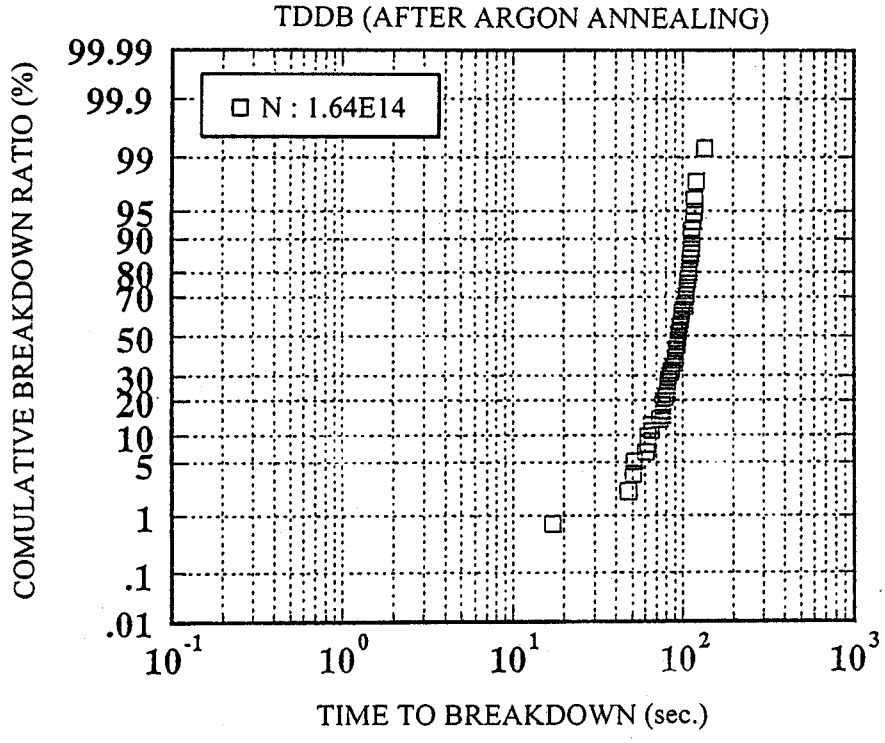


FIG.6(A)

4 FEB 2004

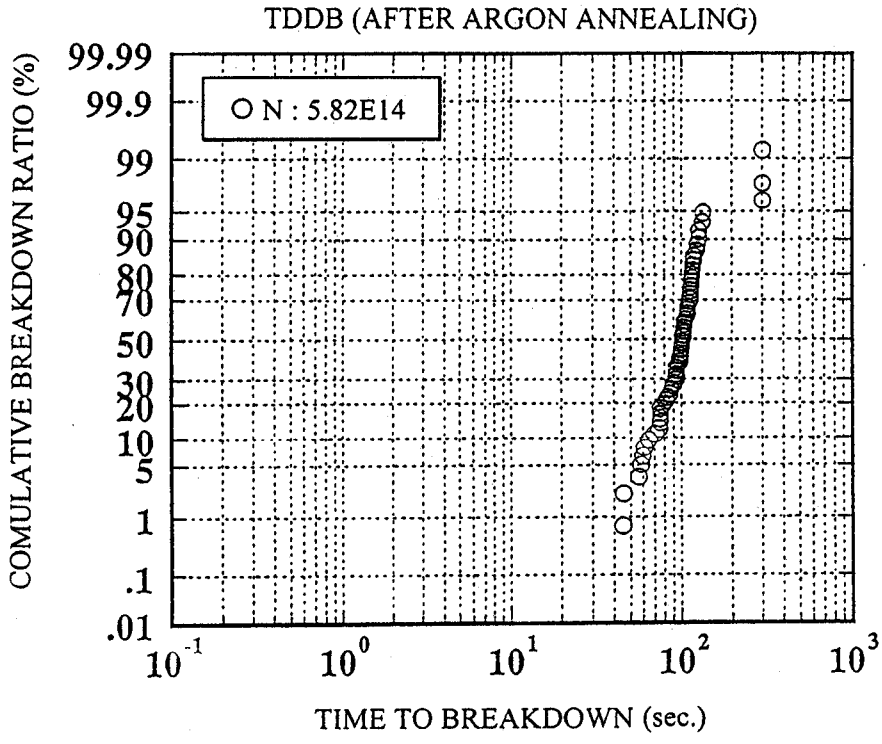


FIG.6(B)

4 FEB 2004

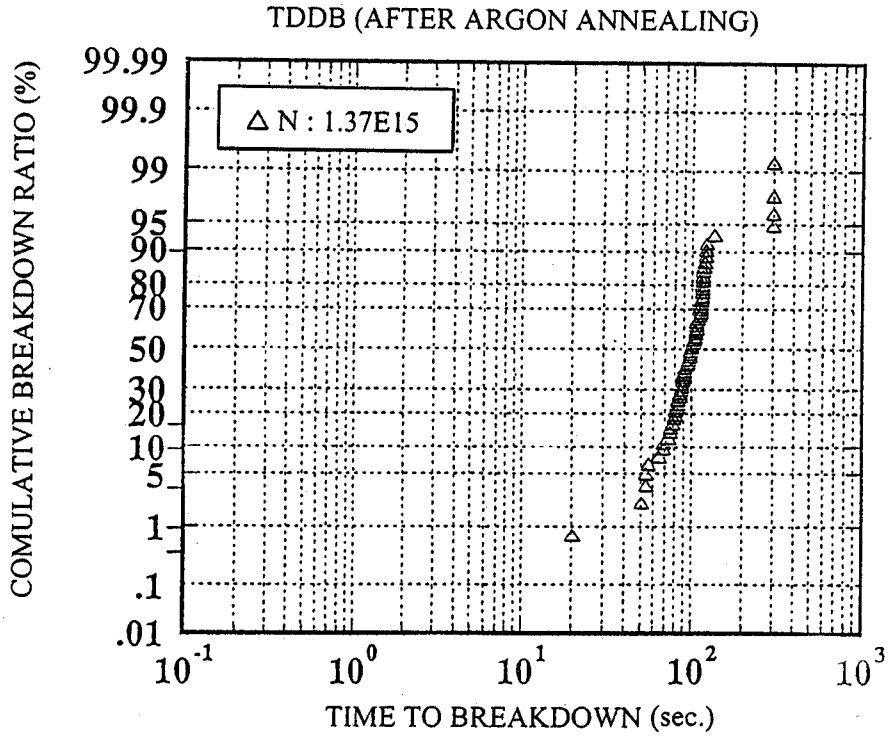


FIG.6(C)

4 FEB 2004

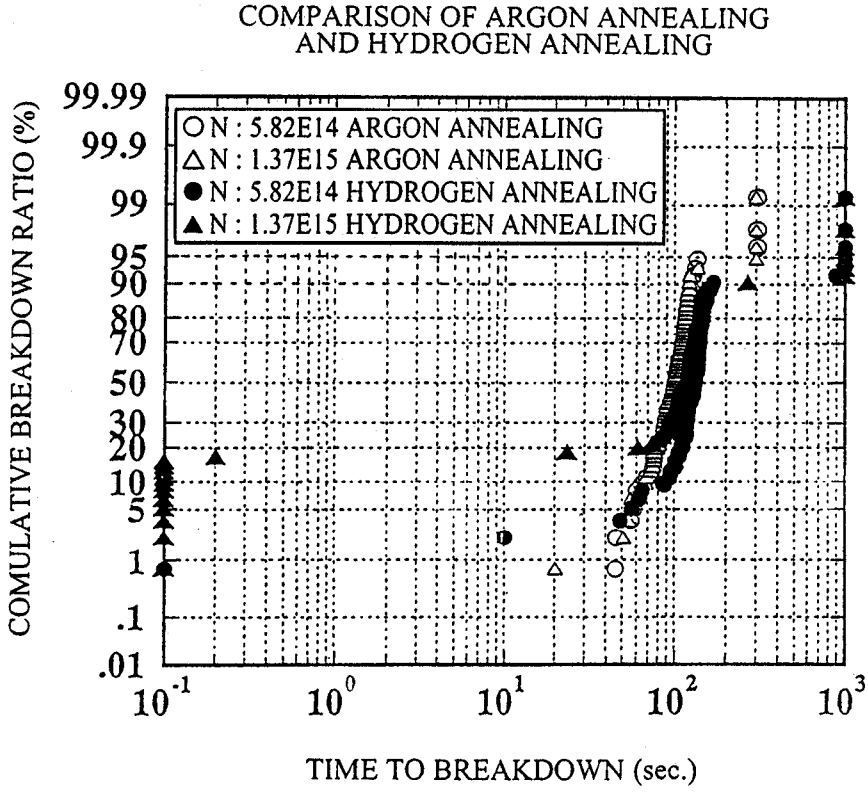


FIG.6(D)

4 FEB 2004

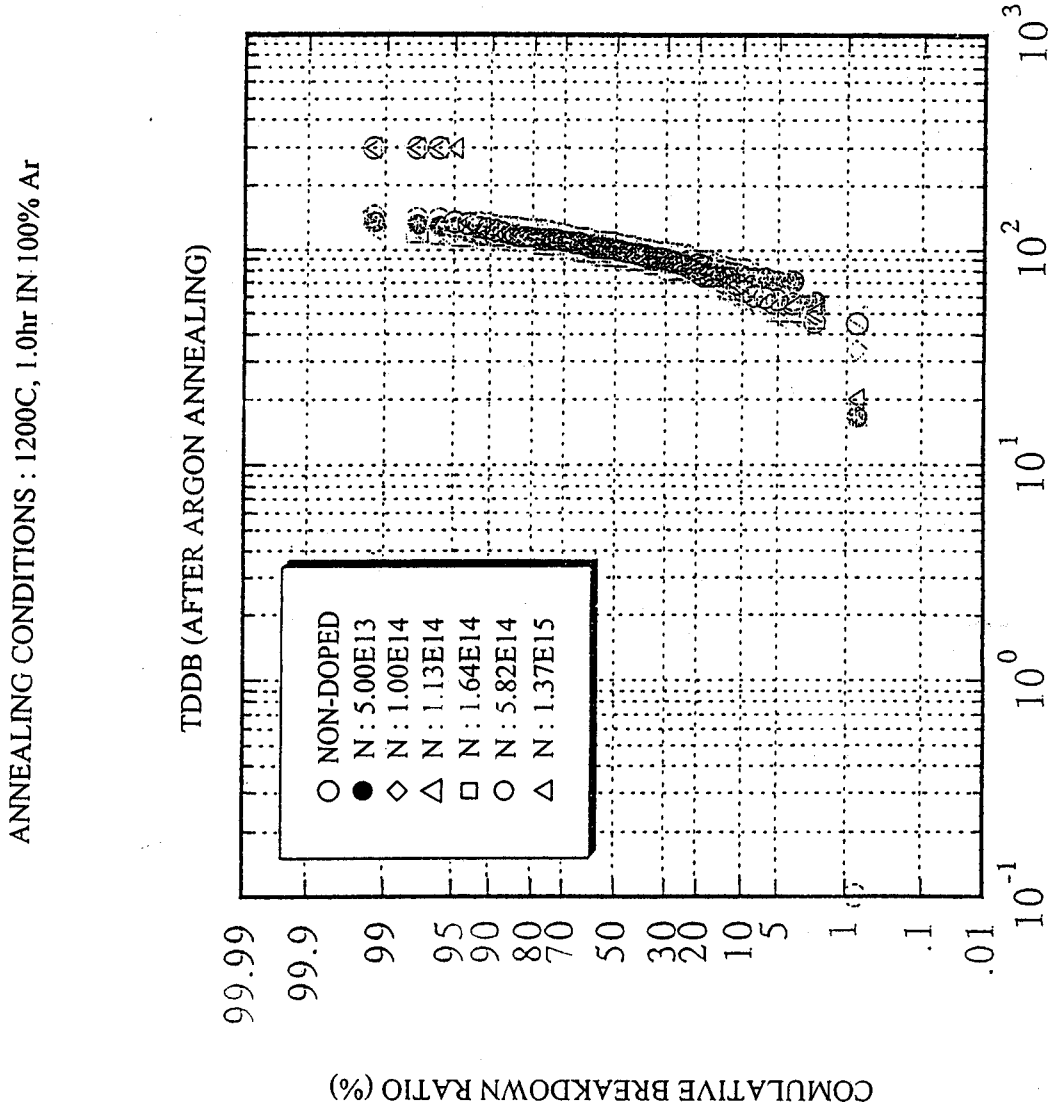


FIG.7

4 FEB 2004

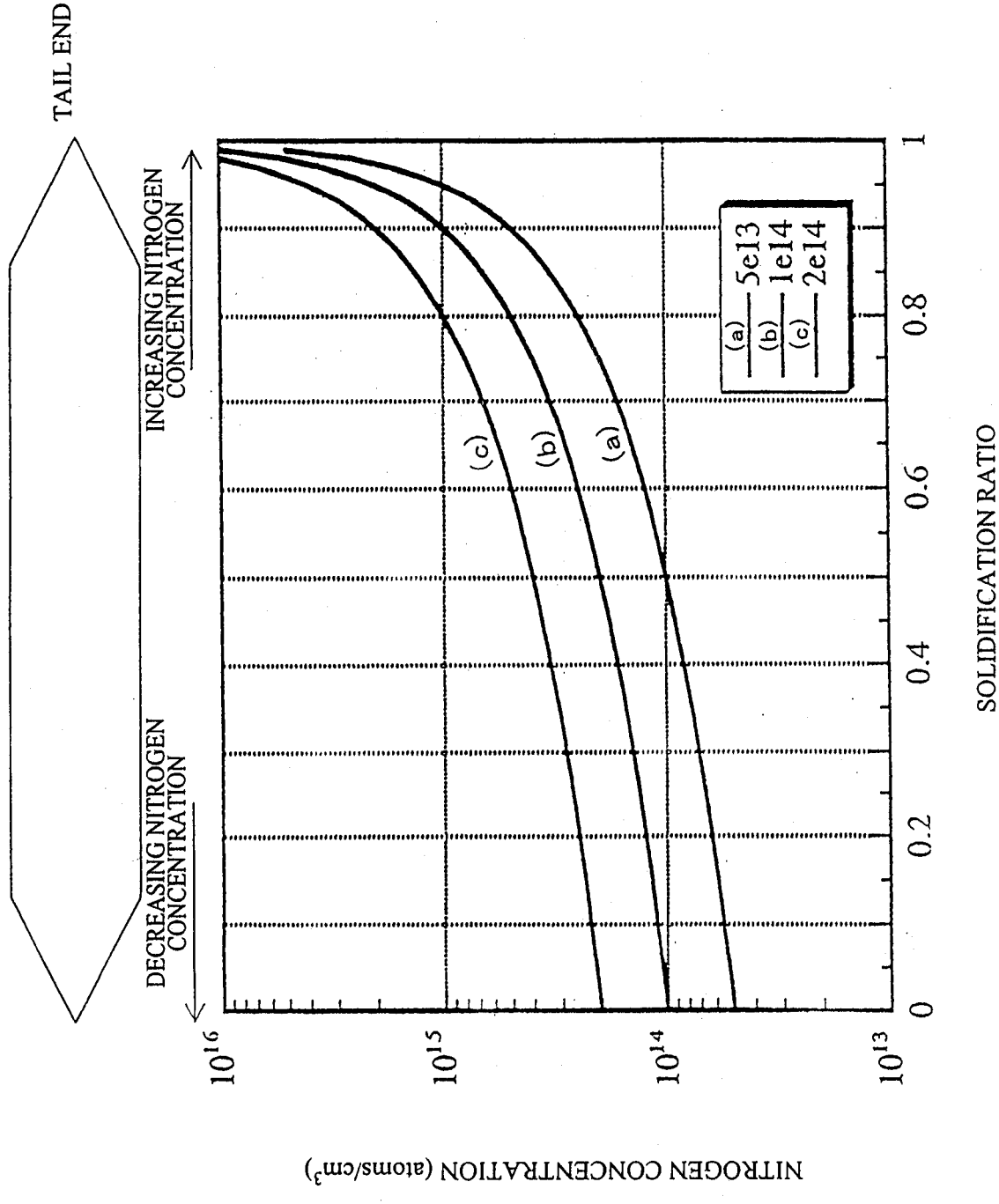


FIG.8